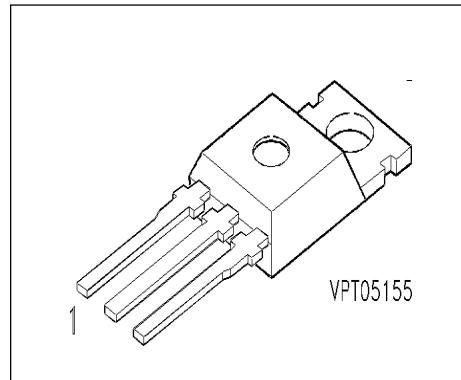


**IGBT**

- Low forward voltage drop
- High switching speed
- Low tail current
- Latch-up free
- Avalanche rated



Pin 1	Pin 2	Pin 3
G	C	E

Type	$V_{CE}$	$I_C$	Package	Ordering Code
SGP30N60	600V	30A	TO-220 AB	Q67040-A . . .

**Maximum Ratings**

Parameter	Symbol	Values	Unit
Collector-emitter voltage	$V_{CE}$	600	V
Collector-gate voltage $R_{GE} = 20 \text{ k}\Omega$	$V_{CGR}$	600	
Gate-emitter voltage	$V_{GE}$	$\pm 20$	
DC collector current $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	$I_C$	58 30	A
Pulsed collector current, $t_p = 1 \text{ ms}$ $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	$I_{Cpuls}$	116 60	
Avalanche energy, single pulse $I_C = 30 \text{ A}$ , $V_{CC} = 50 \text{ V}$ , $R_{GE} = 25 \Omega$ $L = 100 \mu\text{H}$ , $T_j = 25^\circ\text{C}$	$E_{AS}$	65	
Power dissipation $T_C = 25^\circ\text{C}$	$P_{tot}$	250	W

### Preliminary data

#### Maximum Ratings

Parameter	Symbol	Values	Unit
Chip or operating temperature	$T_j$	-55 ... + 150	°C
Storage temperature	$T_{stg}$	-55 ... + 150	
IEC climatic category, DIN IEC 68-1	-	55 / 150 / 56	-

#### Thermal Resistance

Thermal resistance, junction - case	$R_{thJC}$	$\leq 0.5$	K/W
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#### Electrical Characteristics, at $T_j = 25$ °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

#### Static Characteristics

Collector-emitter breakdown voltage $V_{GE} = 0$ V, $I_C = 0.5$ mA, $T_j = -55$ °C	$V_{(BR)CES}$	600	-	-	V
Gate threshold voltage $V_{GE} = V_{CE}$ , $I_C = 0.7$ mA, $T_j = 25$ °C $V_{GE} = V_{CE}$ , $I_C = 0.7$ mA, $T_j = 150$ °C	$V_{GE(th)}$	3 2	4 3	5 -	
Collector-emitter saturation voltage $V_{GE} = 15$ V, $I_C = 30$ A, $T_j = 25$ °C $V_{GE} = 15$ V, $I_C = 30$ A, $T_j = 150$ °C	$V_{CE(sat)}$	1.6 -	2 2.3	2.5 2.8	
Zero gate voltage collector current $V_{CE} = 600$ V, $V_{GE} = 0$ V, $T_j = 25$ °C $V_{CE} = 600$ V, $V_{GE} = 0$ V, $T_j = 150$ °C	$I_{CES}$	- -	- -	40 3000	µA
Gate-emitter leakage current $V_{GE} = 25$ V, $V_{CE} = 0$ V	$I_{GES}$	-	-	100	nA

**Electrical Characteristics**, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**AC Characteristics**

Transconductance $V_{CE} = 20 \text{ V}, I_C = 30 \text{ A}$	$g_{fs}$	6	20	-	S
Input capacitance $V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$	$C_{iss}$	-	1600	2000	pF
Output capacitance $V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$	$C_{oss}$	-	150	190	
Reverse transfer capacitance $V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$	$C_{rss}$	-	90	135	

*Preliminary data*

**Electrical Characteristics**, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**Switching Characteristics, Inductive Load at  $T_j = 150^\circ\text{C}$**

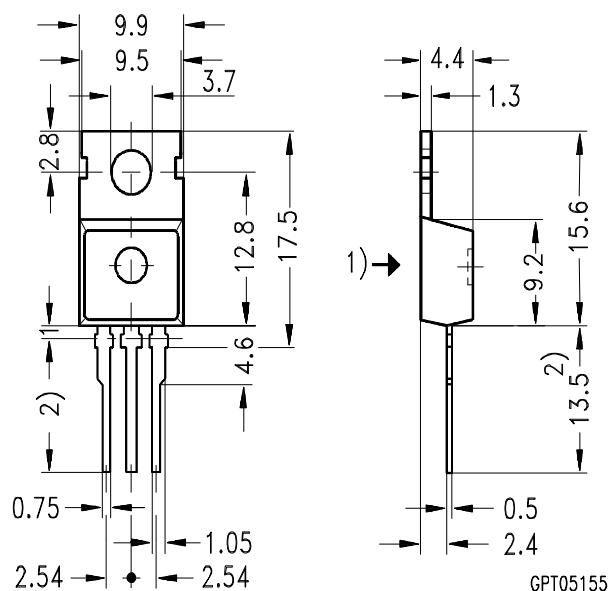
Turn-on delay time $V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 30 \text{ A}$ $R_{Gon} = 11 \Omega$	$t_{d(on)}$	-	30	45	ns
Rise time $V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 30 \text{ A}$ $R_{Gon} = 11 \Omega$	$t_r$	-	45	70	
Turn-off delay time $V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 30 \text{ A}$ $R_{Goff} = 11 \Omega$	$t_{d(off)}$	-	320	480	
Fall time $V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 30 \text{ A}$ $R_{Goff} = 11 \Omega$	$t_f$	-	70	105	
Total turn-on loss energy * $V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 30 \text{ A}$ $R_{Gon} = 11 \Omega, T_j = 150^\circ\text{C}$	$E_{on}$	-	1.81	2.35	mJ
Total turn-off loss energy $V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 30 \text{ A}$ $R_{Goff} = 11 \Omega, T_j = 150^\circ\text{C}$	$E_{off}$	-	0.92	1.2	
Total Gate Charge $V_{CC} = 480 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 30 \text{ A}$	$Q_{G(on)}$	-	140	210	nC

\* includes the reverse recovery losses caused by the FWD of the BUP603D

**Package Outlines**

Dimensions in mm

Weight:



- 1) punch direction, burr max. 0.04
- 2) dip tinning
- 3) max. 14.5 by dip tinning press burr max. 0.05